

# FDN352AP

## Single P-Channel, PowerTrench® MOSFET

### Features

- -1.3 A, -30V  $R_{DS(ON)} = 180 \text{ m}\Omega @ V_{GS} = -10\text{V}$   
-1.1 A, -30V  $R_{DS(ON)} = 300 \text{ m}\Omega @ V_{GS} = -4.5\text{V}$
- High performance trench technology for extremely low  $R_{DS(ON)}$ .
- High power version of industry Standard SOT-23 package. Identical pin-out to SOT-23 with 30% higher power handling capability.

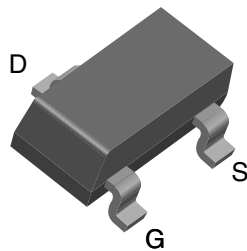
### Applications

- Notebook computer power management

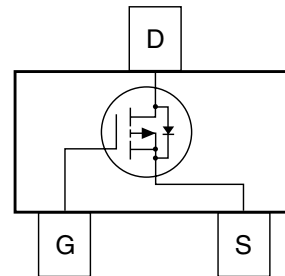
### General Description

This P-Channel Logic Level MOSFET is produced using Fairchild Semiconductor advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain low gate charge for superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss is needed in a very small outline surface mount package.



SuperSOT™-3



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DSS}$	Drain-Source Voltage	-30	V
$V_{GSS}$	Gate-Source Voltage	$\pm 25$	V
$I_D$	Drain Current – Continuous (Note 1a) – Pulsed	-1.3	A
		-10	
$P_D$	Power Dissipation for Single Operation (Note 1a) (Note 1b)	0.5	W
		0.46	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$
<b>Thermal Characteristics</b>			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	250	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	75	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
52AP	FDN352AP	7"	8mm	3000 units

**Electrical Characteristics**  $T_A = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-17		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -24\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSS}$	Gate–Body Leakage	$V_{GS} = \pm 25\text{ V}, V_{DS} = 0\text{ V}$			$\pm 100$	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.8	-2.0	-2.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -10\text{ V}, I_D = -1.3\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -1.1\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -1.1\text{ A}, T_J = 125^\circ\text{C}$		150 250 330	180 300 400	m $\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -0.9\text{ A}$		2.0		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}$		150		pF
$C_{oss}$	Output Capacitance			40		pF
$C_{rss}$	Reverse Transfer Capacitance			20		pF
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -10\text{ V}, R_{GEN} = 6\ \Omega$		4	8	ns
$t_r$	Turn–On Rise Time			15	28	ns
$t_{d(off)}$	Turn–Off Delay Time			10	18	ns
$t_f$	Turn–Off Fall Time			1	2	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -0.9\text{ A},$ $V_{GS} = -4.5\text{ V}$		1.4	1.9	nC
$Q_{gs}$	Gate–Source Charge			0.5		nC
$Q_{gd}$	Gate–Drain Charge			0.5		nC
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				-0.42	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.42\text{ A}$ (Note 2)		-0.8	-1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = -3.9\text{ A},$ $di_F/dt = 100\text{ A}/\mu\text{s}$		17		ns
$Q_{rr}$	Diode Reverse Recovery Charge			7		nC

**Notes:**

1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.

(a)  $R_{\theta JA} = 250^\circ\text{C}/\text{W}$  when mounted on a  $0.02\text{ in}^2$  pad of 2oz. copper.

(b)  $R_{\theta JA} = 270^\circ\text{C}/\text{W}$  when mounted on a  $0.001\text{ in}^2$  pad of 2oz. copper.

2. Pulse Test: Pulse Width <  $300\ \mu\text{s}$ , Duty Cycle < 2.0%

## Typical Characteristics

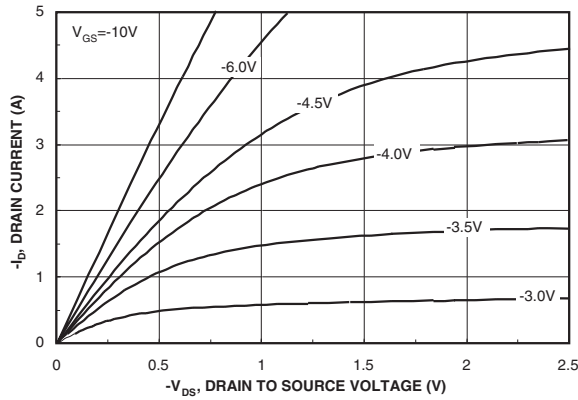


Figure 1. On-Region Characteristics.

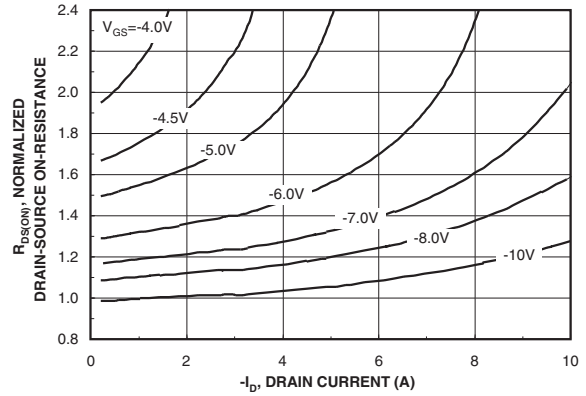


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

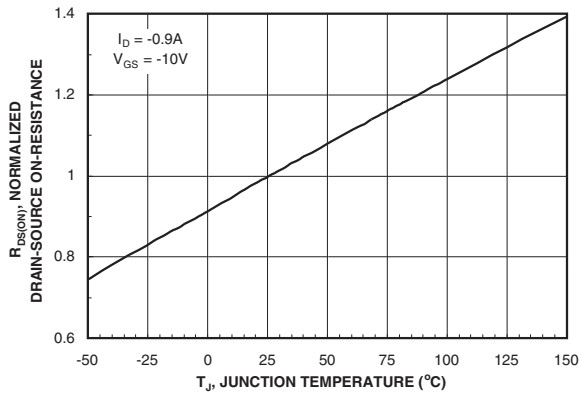


Figure 3. On-Resistance Variation with Temperature.

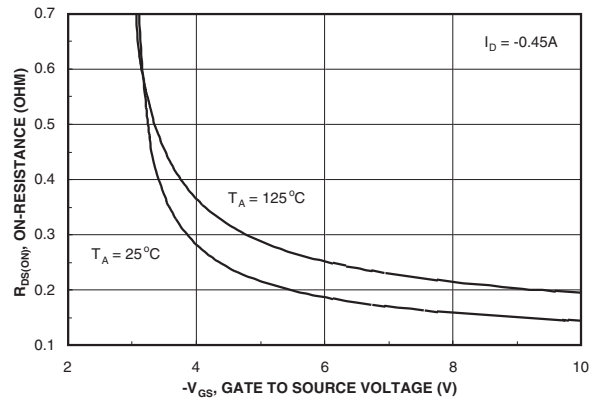


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

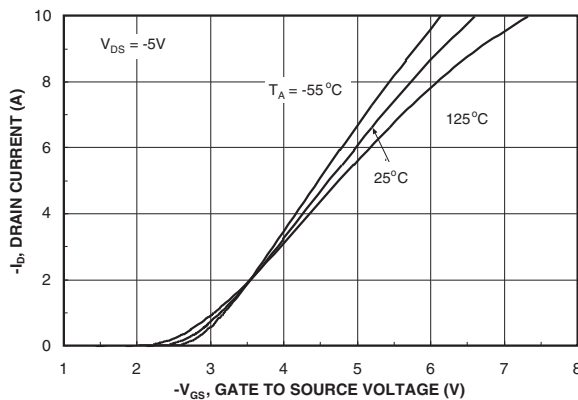


Figure 5. Transfer Characteristics.

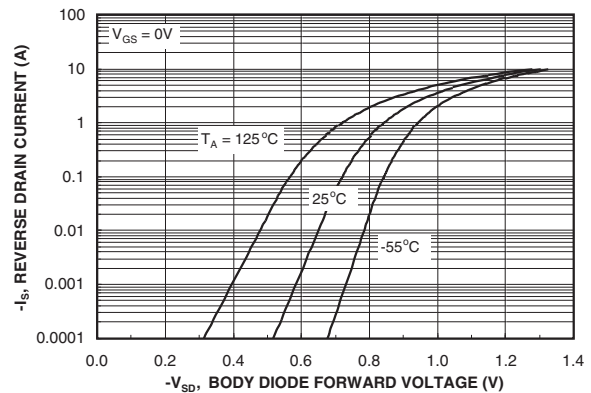


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Characteristics

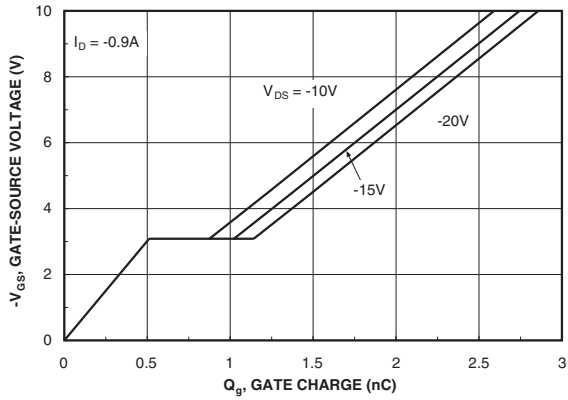


Figure 7. Gate Charge Characteristics.

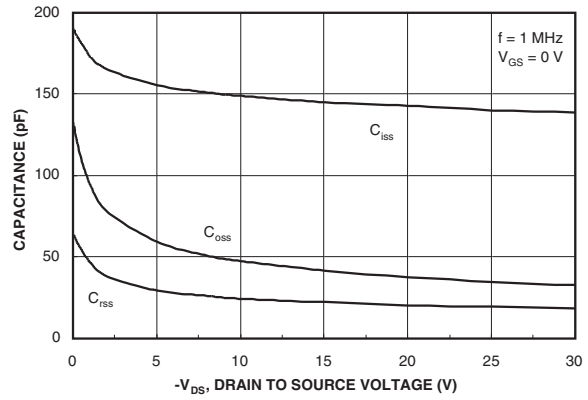


Figure 8. Capacitance Characteristics.

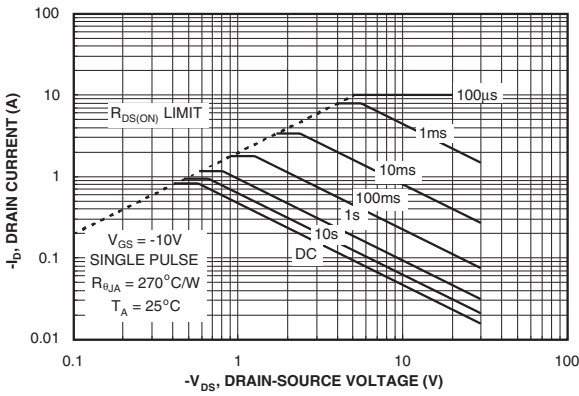


Figure 9. Maximum Safe Operating Area.

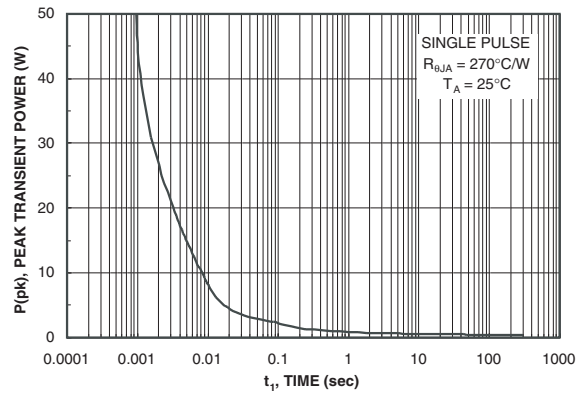


Figure 10. Single Pulse Maximum Power Dissipation.

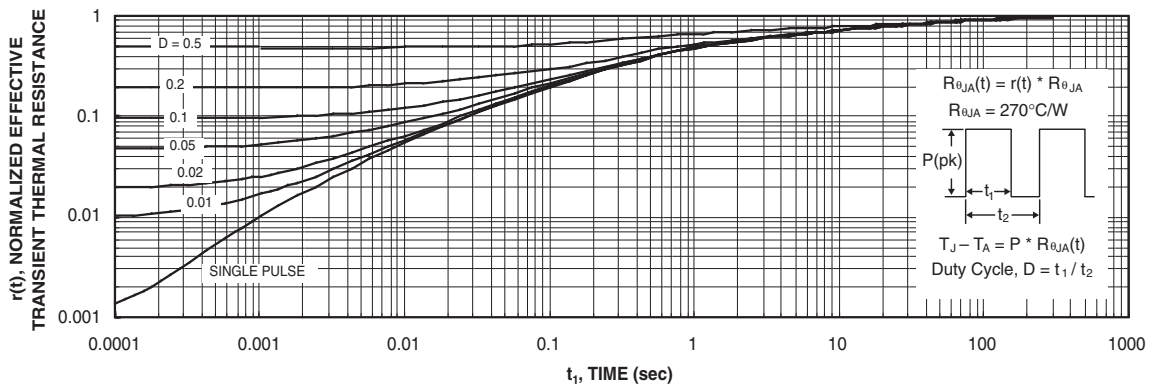


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1b. Transient thermal response will change depending on the circuit board design.

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